

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Doo Yeol RYOO

Serial No.: New Application Group Art Unit: Not Yet Assigned

Filed: July 9, 2003

Examiner: Not Yet Assigned

Title: TRANSISTOR IN SEMICONDUCTOR DEVICES AND METHOD OF FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

July 9, 2003

Sir:

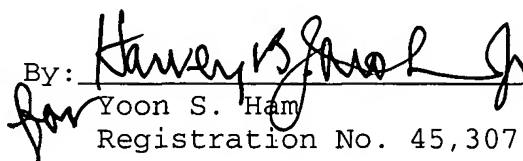
As a means of complying with the duty of disclosure under 37 CFR §1.56, and in accordance with 37 CFR §§1.97 and 1.98, Applicant(s), through the undersigned attorney, submits this Information Disclosure Statement. The patents, publications or other information submitted herewith are listed on the attached Form PTO-1449 and copies are attached.

In accordance with 37 CFR §1.97(b)(1) or (2), this Information Disclosure Statement is being filed either within three months of the filing date of the above-identified application, or within three months of the date of entry into the national stage of the above-identified application as set forth in 37 CFR §1.491. Accordingly, no fee is required.

Respectfully submitted,

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.: P68972US0 GROUP ART UNIT: Not Yet Assigned
 SERIAL NO.: New Application FILING DATE: July 9, 2003
 APPLICANT(S): Doo Yeol RYOO TODAY'S DATE: July 9, 2003

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	INT'L CLASS	SUB- CLASS	FILING DATE (If Appropriate)
AA						
AB						

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION (YES) (NO)
AC						
AD						

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AE C.H.Chen, et al; "Thermally-Enhanced Remote Plasma Nitrided Ultrathin (1.65nm) Gate Oxide with Excellent Performances in Reduction of Leakage Current and Boron Diffusion"; IEEE Electron Device Letters, Vol.22, No. 8; August 2001; pp.378-380.

AF Hoon Lim, et al; "The Effects of STI Process Parameters on the Integrity of Dual Gate Oxides"; IEEE 01CH37167 39th Annual International Reliability Physics Symposium, 2001; pp. 48-51.

AG S.Song, et al; "On the Gate Oxide Scaling of High Performance CMOS Transistors"; 2001 IEEE; IEDM 01-55 to IEDM 01-58.

EXAMINER _____ DATE CONSIDERED _____

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).